

P. Pages : 2

Time : Three Hours



AV - 3298

Max. Marks : 80

- Notes :
1. Due credit will be given to neatness and adequate dimensions.
 2. Assume suitable data wherever necessary.
 3. Illustrate your answer necessary with the help of neat sketches.

1. a) Convert - 8
i) $(A0F9.0EB)_{16}$ to decimal
ii) $(128)_{10}$ to binary
iii) $(463)_8$ to decimal
iv) $(1011011)_{\text{gray}}$ to binary
- b) Perform 2's complement method for following. 2
i) $11011 - 11001$
- c) prove : 4
i) $AB + \bar{A}C + BC = AB + \bar{A}C$
ii) $A + B[AC + (B + \bar{C})D]$

OR

2. Obtain minimal expression using Quine McCluskey methods & realise using NAND gates 14
only
 $f = \sum m(0, 1, 3, 4, 5, 7, 10, 13, 14, 15)$
3. a) Compare TTL, ECL, MOS & CMOS logic families. 6
b) What is tristate logic ? Explain TSL inverter. 7

OR

4. a) What is race around condition ? How is it overcome ? 7
b) Design Modulo - 12 asynchronous binary ripple counter. 6
5. a) Design a 40:1 multiplexer using 8:1 MUX. 7
b) Design a 5-bit comparator using IC 7485. 6

OR

6. a) Design 10-bit even parity generator using 74180. 7
b) Explain decimal to BCD encoder IC 74147 & its working. 6

7. a) Draw and explain block diagram of PLA. 7
b) Design a combinational circuit using ROM. The circuit accepts a 3-bit number and generates an output binary number equal to square of input number. 7

OR

8. a) Draw and explain FPGA architecture. 7
b) Explain carry look ahead adder. 7
9. a) Draw and explain 4-phase ratio less shift register. 7
b) Explain dynamic MOSRAM cell. 6

OR

10. a) Draw & explain BJT RAM cell. 7
b) Explain CCD memory operation. 6
11. Design a sequence detector to detect 1010, if the input sequence is 01101010. 13

OR

12. a) State & explain general models of sequential machines. 6
b) A sequential circuit with two DFF A and B, two inputs x & y and one output Z is specified by following equation ? 7
$$A_{n+1} = \bar{x}y + xA_n$$
$$B_{n+1} = \bar{x}B + xA$$
$$Z = B_n$$

i) Draw state table
ii) Draw state diagram.
